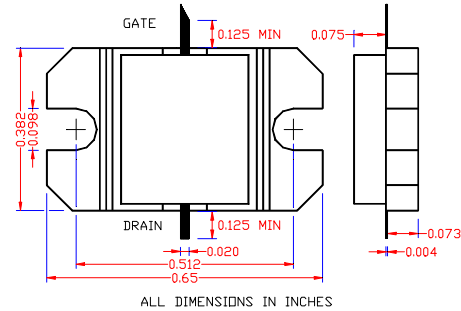


Not recommended for new designs. Contact factory. Effective 03/2003
10.7-11.7GHz, 4W Internally Matched Power FET

- **10.7-11.7GHz BANDWIDTH AND INPUT/OUTPUT IMPEDANCE MATCHED TO 50 OHM**
- **EIA FEATURES HIGH PAE(30% TYPICAL)**
- **EIB FEATURES HIGH IP3(49dBm TYPICAL)**
- **+36.5/+35.5dBm TYPICAL P_{1dB} OUTPUT POWER FOR EIA/EIB**
- **9/8dB TYPICAL G_{1dB} POWER GAIN FOR EIA/EIB**
- **NON-HERMETIC METAL FLANGE PACKAGE**


ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOLS	PARAMETERS/TEST CONDITIONS	EIA1011-4P			EIB1011-4P			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
P_{1dB}	Output Power at 1dB Compression f=10.7-11.7GHz V _{ds} =8V, I _d sq=0.5 I _{dss} (EIA), 0.6I _{dss} (EIB)	35.5	36.5		35	35.5		dBm
G_{1dB}	Gain at 1dB Compression f=10.7-11.7GHz V _{ds} =8V, I _d sq=0.5 I _{dss} (EIA), 0.6I _{dss} (EIB)	8	9		7	8		dB
PAE	Power Added Efficiency at 1dB compression f=10.7-11.7GHz V _{ds} =8V, I _d sq=0.5 I _{dss} (EIA), 0.6I _{dss} (EIB)		30			25		%
I_d1dB	Drain Current at 1dB Compression		1760			1700		mA
IP3	Output 3 rd Order Intercept Point f=10.7-11.7GHz V _{ds} =8V, I _d sq=0.5 I _{dss} (EIA), 0.6I _{dss} (EIB)		43			49*		dBm
I_{dss}	Saturated Drain Current V _{ds} =3V, V _{gs} =0V	2200	2880	3400	2200	2720	3400	mA
G_m	Transconductance V _{ds} =3V, V _{gs} =0V		3000			1400		mS
V_p	Pinch-off Voltage V _{ds} =3V, I _d s=24mA		-1.0	-2.5		-2.0	-3.5	V
BV_{gd}	Drain Breakdown Voltage I _{gd} =9.6mA	-13	-15			-15		V
R_{th}	Thermal Resistance (Au-Sn Eutectic Attach)		4.5			4.5		°C/W

*Typical -45dBc IM3 at P_{out}=26dBm/Tone

MAXIMUM RATINGS AT 25°C

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	12V	8V
V_{gs}	Gate-Source Voltage	-8V	-3V
I_{ds}	Drain Current	I _{dss}	3120mA
I_{gsf}	Forward Gate Current	360mA	60mA
P_{in}	Input Power	35dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175°C	150°C
T_{stg}	Storage Temperature	-65/175°C	-65/150°C
P_t	Total Power Dissipation	30W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.